emitting layer positioned between said bottom cladding layer and said upper cladding layer, said epitaxial structure having a window layer positioned on said upper cladding layer;

an ohmic contact electrode positioned on said epitaxial structure; and

a current blocking structure positioned inside said epitaxial structure, said current blocking structure extending from a region below said ohmic contact electrode to at least said light-emitting layer, said current blocking structure having an area that is smaller than an area of said ohmic contact electrode, said current blocking structure extending to said bottom cladding layer.

23. (new) The light-emitting device of Claim 22, further comprising:

a contact layer means positioned between said window layer and said ohmic contact electrode, said contact layer means for spreading current laterally.

24. (new) The light-emitting device of Claim 22, said ohmic contact electrode having a bottom surface, said current blocking structure extending from said bottom surface of said ohmic contract electrode.